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ภาคผนวก ก

บทความที่ได้รับการตีพิมพ์เผยแพร่

บทความที่ได้รับการตีพิมพ์เผยแพร่

รายชื่อบทความวิจัยที่ได้รับการตีพิมพ์

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ภาคผนวก ข

รายละเอียดข้อมูลต่าง ๆ ของอุปกรณ์ที่ใช้
สำหรับวงจรเรียงกระแสหนึ่งเฟสแบบบริดจ์และวงจรแปลงผันแบบบัคก์

FAIRCHILD
SEMICONDUCTOR®

GBPC 12, 15, 25, 35 SERIES

Bridege Rectifiers (Glass Passivated)

Features

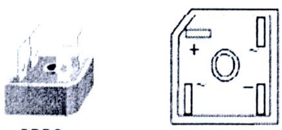
- Integrally molded heatsink provided very low thermal resistance for maximum heat dissipation.
- Surge ovrload rartings from 300 amperes to 400 amperes.
- Isolated voltage from case to lead over 2500 volts.
- UL certified, UL #E96005

Suffix "W"

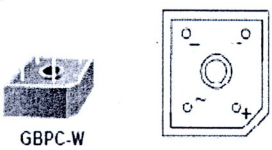
Wire Lead Structure

Suffix "M"

Terminal Location Face to Face



GBPC



GBPC-W

Absolute Maximum Ratings * T_A = 25°C unless otherwise noted

Symbol	Parameter	Value							Units
		005	01	02	04	06	08	10	
V_{RRM}	Maximum Repetitive Reverse Voltage	50	100	200	400	600	800	1000	V
V_{RMS}	Maximum RMS Bridge Input Voltage	35	70	140	280	420	560	700	V
V_R	DC Reverse Voltage (Rated V_R)	50	100	200	400	600	800	1000	V
$I_{F(AV)}$	Average Recitified Forward Current @ T_A = 55°C GBPC12 / GBPC15 / GBPC25 / GBPC35	12 / 15 / 25 / 35							A / A / A / A
I_{FSM}	Non-Repetitive Peak Forward Surge Current GBPC12, 25, 25 / 8.3ms Single Half-Sine-Wave GBPC35	300 / 400							A / A
T_{STG}	Storage Temperature Range	-55 to +150							°C
T_J	Operating Junction Temperature	-55 to +150							°C

* These ratings are limiting values above which the serviceability of any semiconductor device may by impaired.

Thermal Characteristics

Symbol	Parameter	Value	Units
P_D	Power Dissipation	83.3	W
$R_{\theta JL}$	Thermal Resistance, Junction to Lead	1.5	°C/W

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_F	Forward Voltage Drop, per bridge @6.0A GBPC12 @7.5A GBPC15 @12.5A GBPC25 @17.5A GBPC35	1.1 (Max.)	V
I_R	Reverse Current, per element @ Rated V_R T_A = 25°C T_A = 125°C	5.0 (Max.) 500 (Max.)	μA μA
	I^2t Rating for Fusing t < 8.35ms GBPC12, 15, 25 GBPC35	375 660	A^2Sec A^2Sec
C_T	Total Capcitance, per leg V_R = 4.0V GBPC12, 15, 25 f = 1.0MHz GBPC35	180 200	pF pF

Typical Performance Characteristics

Figure 1. Forward Current Derating Curve

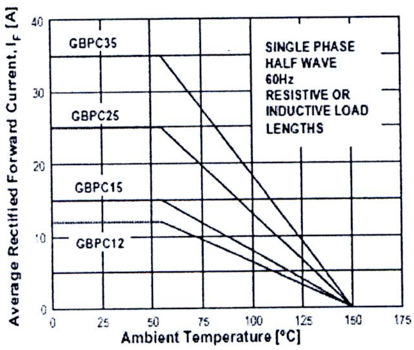


Figure 2. Non-Repetitive Surge Current

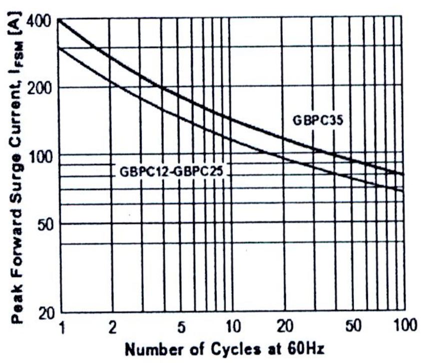


Figure 3. Forward Voltage Characteristics

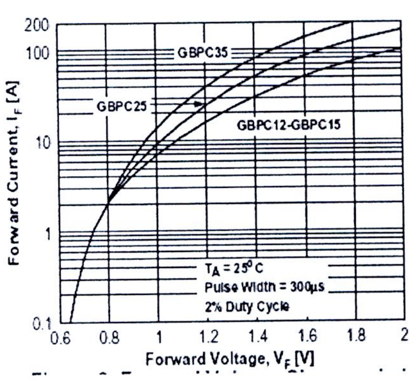
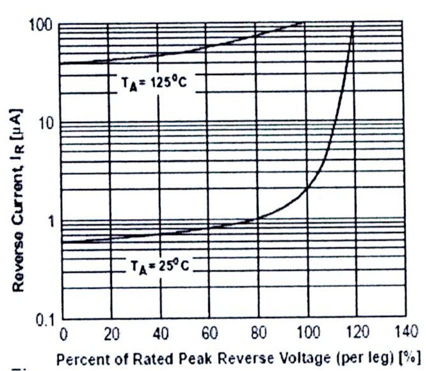


Figure 4. Reverse Current vs Reverse Voltage



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ActiveArray™	FASTr™	LittleFET™	PowerEdge™	SuperFET™
Bottomless™	FPS™	MICROCOUPLER™	PowerSaver™	SuperSOT™-3
CoolFET™	FRFET™	MicroFET™	PowerTrench®	SuperSOT™-6
CROSSVOLT™	GlobalOptoisolator™	MicroPak™	QFET®	SuperSOT™-8
DOME™	GTO™	MICROWIRE™	QS™	SyncFET™
EcoSPARK™	HiSeC™	MSX™	QT Optoelectronics™	TinyLogic®
E²CMOS™	I²C™	MSXPro™	Quiet Series™	TINYOPTO™
EnSigna™	*i-Lo*™	OCX™	RapidConfigure™	TruTranslation™
FACT™	ImpliedDisconnect™	OCXPro™	RapidConnect™	UHC™
FACT Quiet Series™		OPTOLOGIC®	µSerDes™	UltraFET®
Across the board. Around the world.™		OPTOPLANAR™	SILENT SWITCHER®	UniFET™
The Power Franchise®		PACMAN™	SMART START™	VCX™
Programmable Active Droop™		POP™	SPM™	

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As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

Rev. I4

MUR1510, MUR1515, MUR1520, MUR1540, MUR1560

Preferred Devices

SWITCHMODE™ Power Rectifiers

. . . designed for use in switching power supplies, inverters and as free wheeling diodes, these state–of–the–art devices have the following features:

- Ultrafast 35 and 60 Nanosecond Recovery Time
- 175°C Operating Junction Temperature
- Popular TO–220 Package
- High Voltage Capability to 600 Volts
- Low Forward Drop
- Low Leakage Specified @ 150°C Case Temperature
- Current Derating Specified @ Both Case and Ambient Temperatures

Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 1.9 grams (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Shipped 50 units per plastic tube
- Marking: U1510, U1515, U1520, U1540, U1560

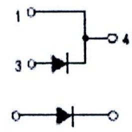
MAXIMUM RATINGS

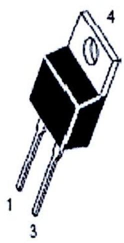
Please See the Table on the Following Page

ON Semiconductor™

http://onsemi.com

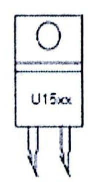
ULTRAFAST RECTIFIERS 15 AMPERES 100–600 VOLTS





TO–220AC
CASE 221B
PLASTIC

MARKING DIAGRAM



U15xx = Device Code
xx = 10, 15, 20, 40 or 60

ORDERING INFORMATION

Device	Package	Shipping
MUR1510	TO–220	50 Units/Rail
MUR1515	TO–220	50 Units/Rail
MUR1520	TO–220	50 Units/Rail
MUR1540	TO–220	50 Units/Rail
MUR1560	TO–220	50 Units/Rail

Preferred devices are recommended choices for future use and best overall value.

MUR1510, MUR1515, MUR1520, MUR1540, MUR1560

MAXIMUM RATINGS

Rating	Symbol	MUR 1510	1515	1520	1540	1560	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	100	150	200	400	600	Volts
Average Rectified Forward Current (Rated V_R)	$I_{F(AV)}$	15 @ T_C = 150°C				15 @ T_C = 145°C	Amps
Peak Rectified Forward Current (Rated V_R, Square Wave, 20 kHz)	I_{FRM}	30 @ T_C = 150°C				30 @ T_C = 145°C	Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	200			150		Amps
Operating Junction Temperature and Storage Temperature Range	T_J, T_{stg}	–65 to +175					°C

THERMAL CHARACTERISTICS

Maximum Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.5	°C/W

ELECTRICAL CHARACTERISTICS

Maximum Instantaneous Forward Voltage (Note 1.) (i_F = 15 Amps, T_C = 150°C) (i_F = 15 Amps, T_C = 25°C)	v_F	0.85 1.05	1.12 1.25	1.20 1.50	Volts
Maximum Instantaneous Reverse Current (Note 1.) (Rated dc Voltage, T_C = 150°C) (Rated dc Voltage, T_C = 25°C)	i_R	500 10	500 10	1000 10	µA
Maximum Reverse Recovery Time (I_F = 1.0 Amp, di/dt = 50 Amps/µs)	t_{rr}	35	60		ns

1. Pulse Test: Pulse Width = 300 µs, Duty Cycle ≤ 2.0%.

MUR1510, MUR1515, MUR1520, MUR1540, MUR1560

MUR1510, MUR1515, MUR1520

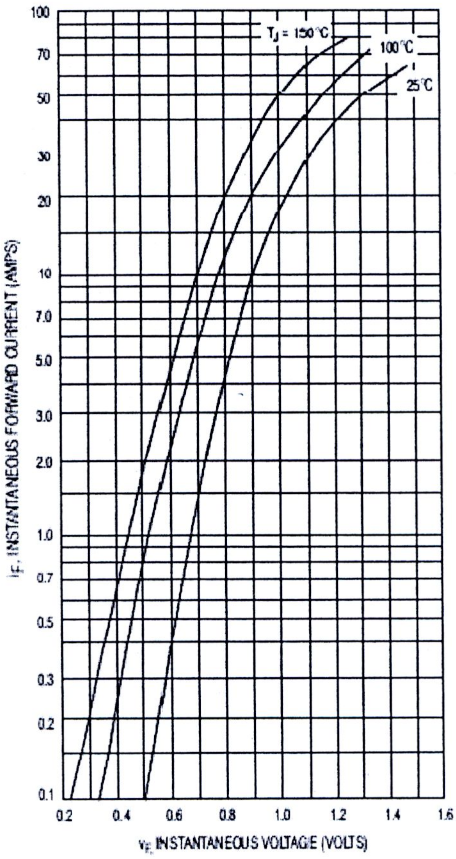


Figure 1. Typical Forward Voltage

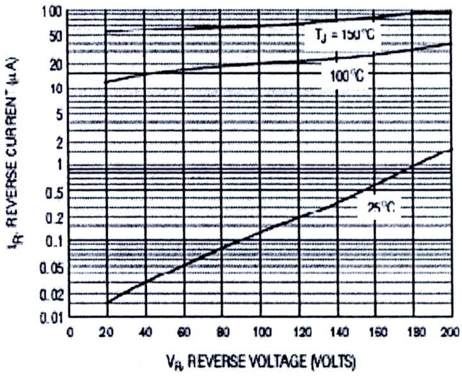


Figure 2. Typical Reverse Current

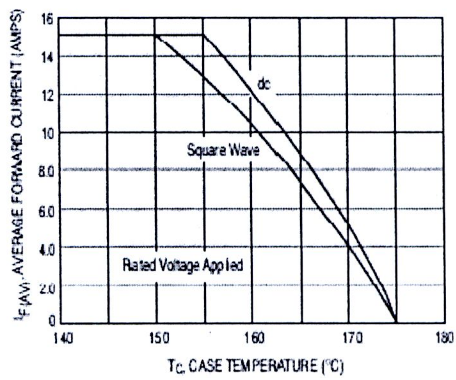


Figure 3. Current Derating, Case

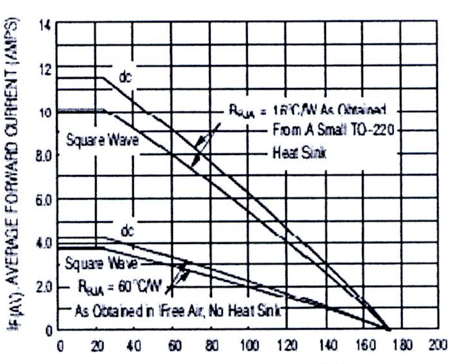


Figure 4. Current Derating, Ambient

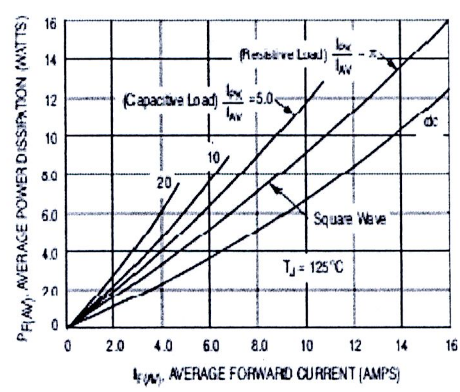


Figure 5. Power Dissipation

MUR1510, MUR1515, MUR1520, MUR1540, MUR1560

MUR1540

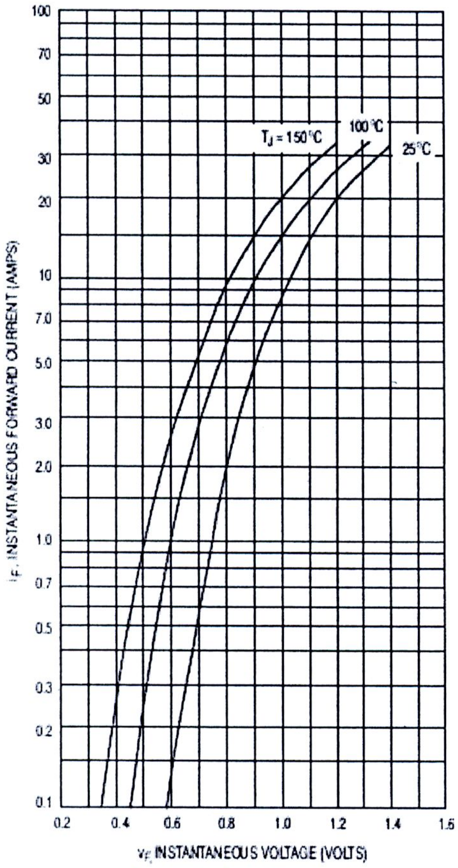


Figure 6. Typical Forward Voltage

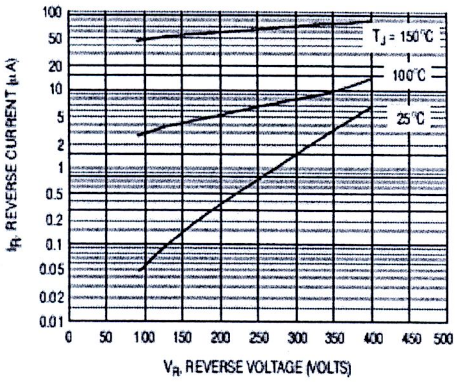


Figure 7. Typical Reverse Current

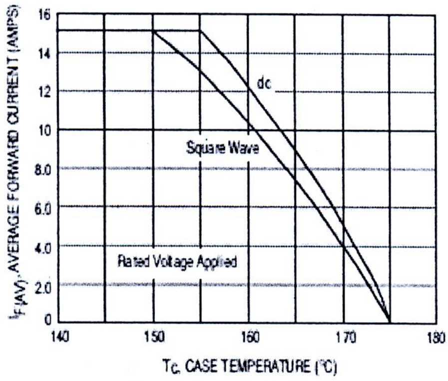


Figure 8. Current Derating, Case

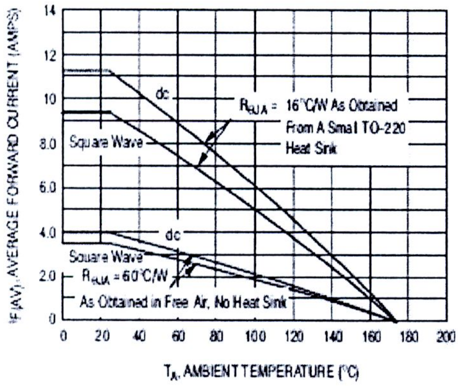


Figure 9. Current Derating, Ambient

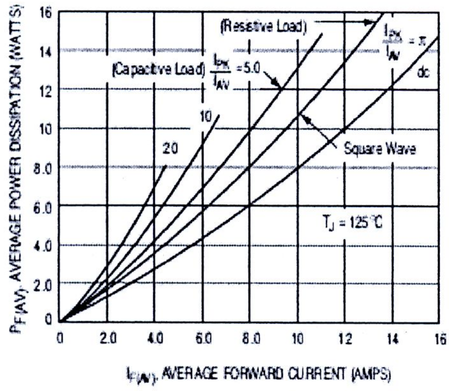


Figure 10. Power Dissipation

MUR1510, MUR1515, MUR1520, MUR1540, MUR1560

MUR1560

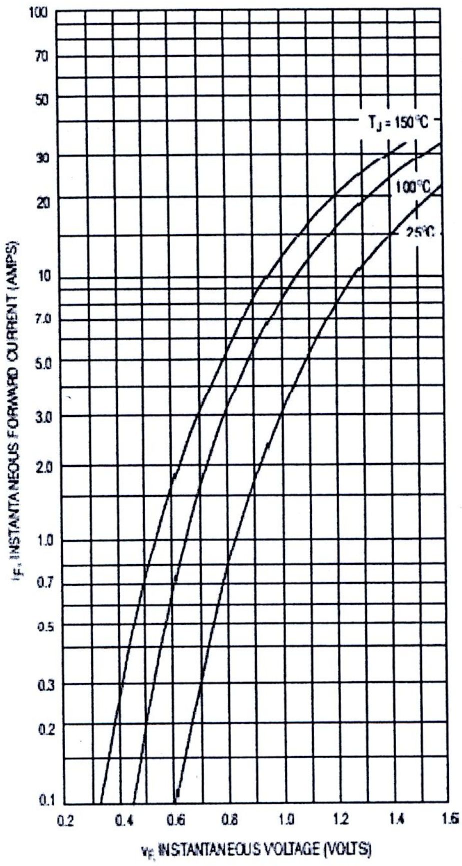


Figure 11. Typical Forward Voltage

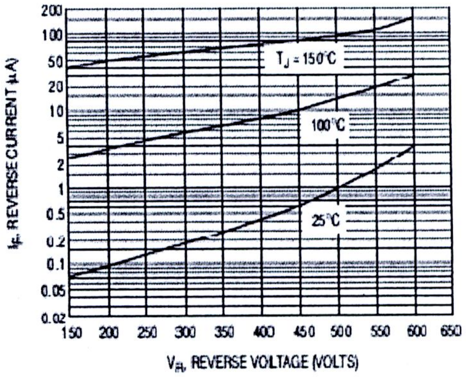


Figure 12. Typical Reverse Current

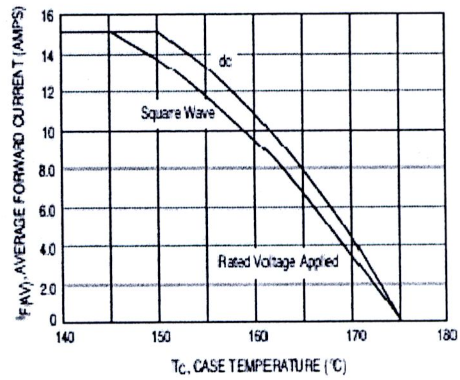


Figure 13. Current Derating, Case

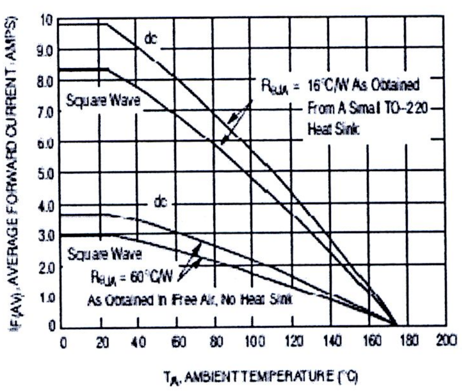


Figure 14. Current Derating, Ambient

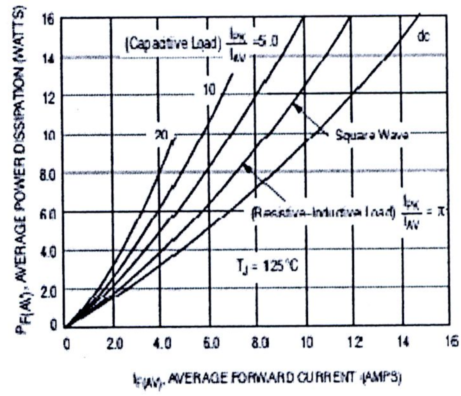


Figure 15. Power Dissipation

MUR1510, MUR1515, MUR1520, MUR1540, MUR1560

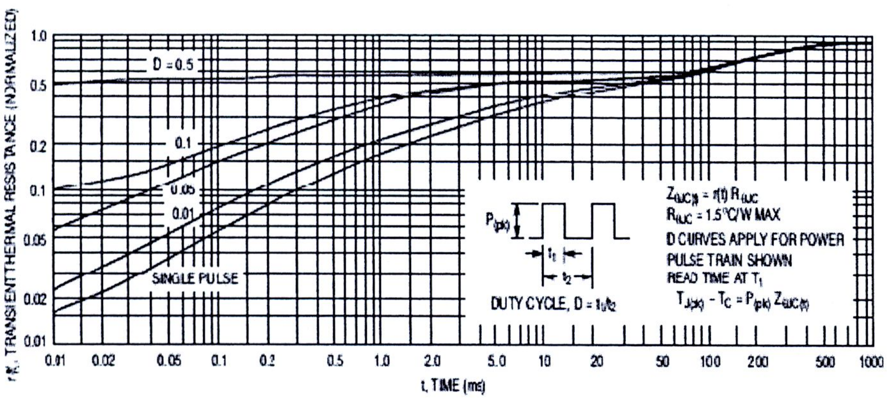


Figure 16. Thermal Response

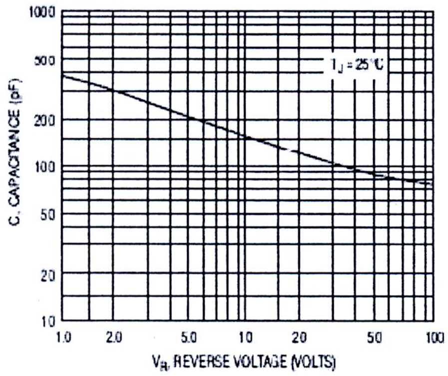
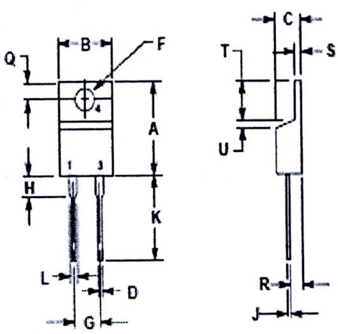


Figure 17. Typical Capacitance

MUR1510, MUR1515, MUR1520, MUR1540, MUR1560

PACKAGE DIMENSIONS

TO–220 TWO–LEAD
CASE 221B–04
ISSUE D



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

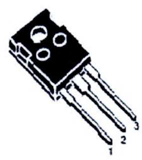
DIM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	0.595	0.620	15.11	15.75
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.82
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.190	0.210	4.83	5.33
H	0.110	0.130	2.79	3.30
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.14	1.52
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.14	1.39
T	0.235	0.255	5.97	6.48
U	0.000	0.050	0.000	1.27

STW12NK80Z

N-CHANNEL 800V - 0.65Ω - 10.5A TO-247
Zener-Protected SuperMESH™ Power MOSFET

TYPE	V_{DSS}	$R_{DS(on)}$	I_D	Pw
STW12NK80Z	800 V	< 0.75 Ω	10.5 A	190 W

- TYPICAL $R_{DS}(on)$ = 0.65 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- GATE CHARGE MINIMIZED
- VERY LOW INTRINSIC CAPACITANCES
- VERY GOOD MANUFACTURING REPEATIBILITY

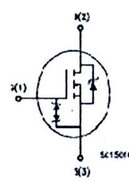


TO-247

DESCRIPTION

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

INTERNAL SCHEMATIC DIAGRAM



APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- IDEAL FOR OFF-LINE POWER SUPPLIES

ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STW12NK80Z	W12NK80Z	TO-247	TUBE

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	800	V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	800	V
V_{GS}	Gate- source Voltage	± 30	V
I_D	Drain Current (continuous) at T_C = 25°C	10.5	A
I_D	Drain Current (continuous) at T_C = 100°C	6.6	A
I_{DM} (•)	Drain Current (pulsed)	42	A
P_{TOT}	Total Dissipation at T_C = 25°C	190	W
	Derating Factor	1.51	W/°C
$V_{ESD(G-S)}$	Gate source ESD(HBM-C=100pF, R=1.5KΩ)	6000	V
dv/dt (1)	Peak Diode Recovery voltage slope	4.5	V/ns
T_j T_{stg}	Operating Junction Temperature Storage Temperature	-55 to 150	°C

(•) Pulse width limited by safe operating area
(1) $I_{SD} \leq 10.5A$, $di/dt \leq 200A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{JMAX}$
(*) Limited only by maximum temperature allowed

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	0.66	°C/W
Rthj-amb T_l	Thermal Resistance Junction-ambient Max Maximum Lead Temperature For Soldering Purpose	50 300	°C/W °C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	10.5	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	400	mJ

GATE-SOURCE ZENER DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV_{GSO}	Gate-Source Breakdown Voltage	Igs=± 1mA (Open Drain)	30			V

PROTECTION FEATURES OF GATE-TO-SOURCE ZENER DIODES

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

ELECTRICAL CHARACTERISTICS (T_{CASE} =25°C UNLESS OTHERWISE SPECIFIED)

ON/OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 1 mA, V_{GS} = 0	800			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating V_{DS} = Max Rating, T_C = 125 °C			1 50	µA µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 20V			±10	µA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 100 µA	3	3.75	4.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10V, I_D = 5.25 A		0.65	0.75	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	V_{DS} = 15 V, I_D = 5.25 A		12		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		2620 250 53		pF pF pF
$C_{oss\ eq.}$ (3)	Equivalent Output Capacitance	V_{GS} = 0V, V_{DS} = 0V to 640V		100		pF

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	V_{DD} = 400 V, I_D = 5.25 A R_G = 4.7Ω V_{GS} = 10 V (Resistive Load see, Figure 3)		30 18		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 640V, I_D = 10.5 A, V_{GS} = 10V		87 14 44		nC nC nC

SWITCHING OFF

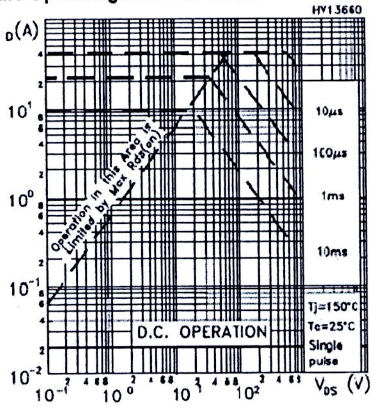
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	V_{DD} = 400 V, I_D = 5.25 A R_G = 4.7Ω V_{GS} = 10 V (Resistive Load see, Figure 3)		70 20		ns ns
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	V_{DD} = 640 V, I_D = 10.5 A, R_G = 4.7Ω, V_{GS} = 10V (Inductive Load see, Figure 5)		16 15 28		ns ns ns

SOURCE DRAIN DIODE

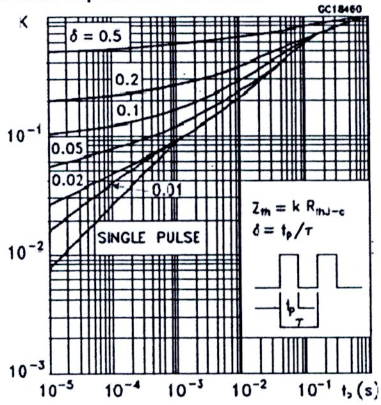
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM} (2)	Source-drain Current Source-drain Current (pulsed)				10.5 42	A A
V_{SD} (1)	Forward On Voltage	I_{SD} = 10.5 A, V_{GS} = 0			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 10.5 A, di/dt = 100A/µs V_{DD} = 100 V, T_j = 150°C (see test circuit, Figure 5)		635 5.9 18.5		ns µC A

Note: 1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. Pulse width limited by safe operating area.
3. $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.

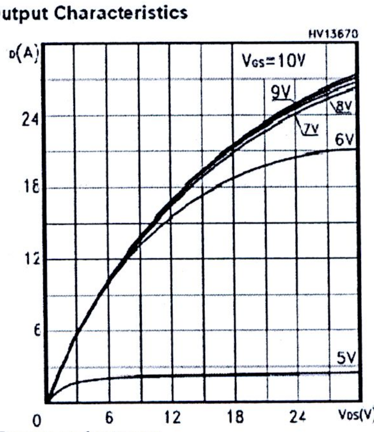
Safe Operating Area For TO-247



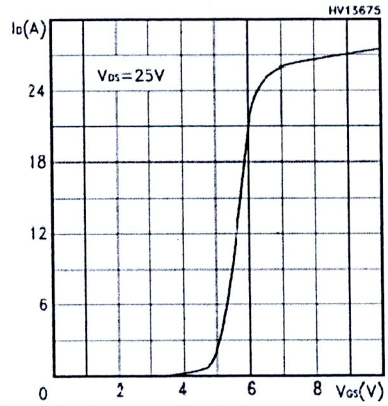
Thermal Impedance For TO-247



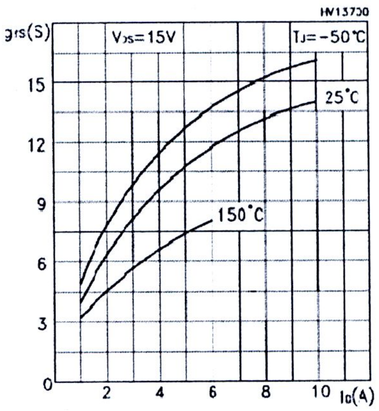
Output Characteristics



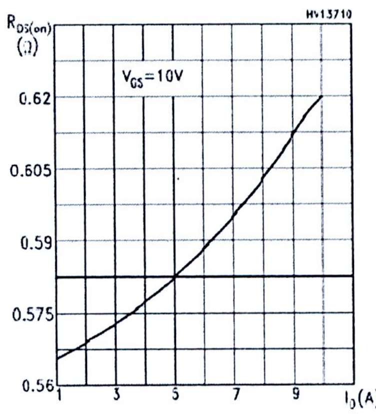
Transfer Characteristics



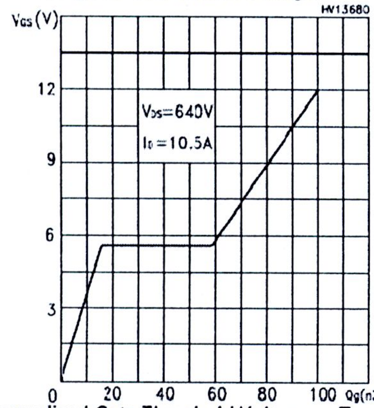
Transconductance



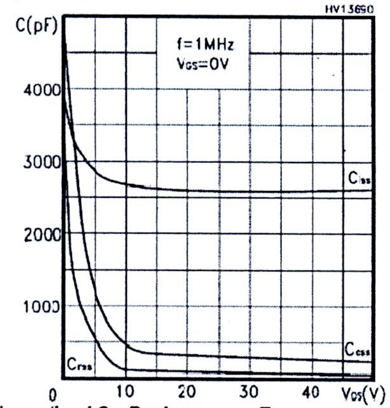
Static Drain-source On Resistance



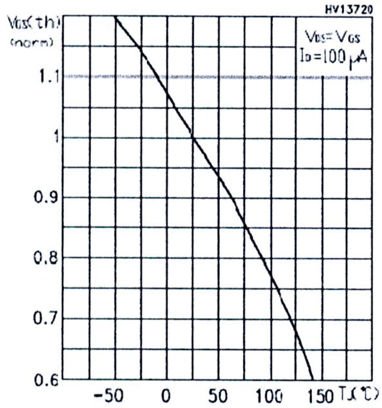
Gate Charge vs Gate-source Voltage



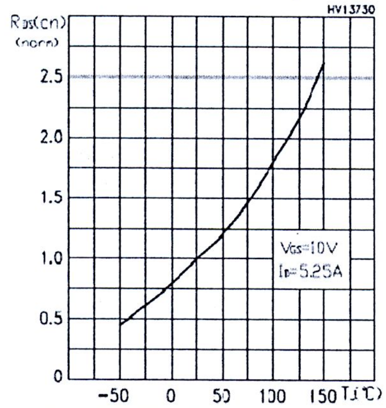
Capacitance Variations



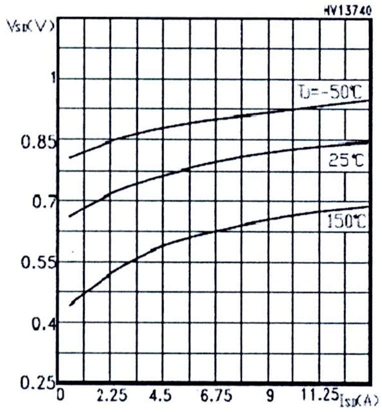
Normalized Gate Threshold Voltage vs Temp.



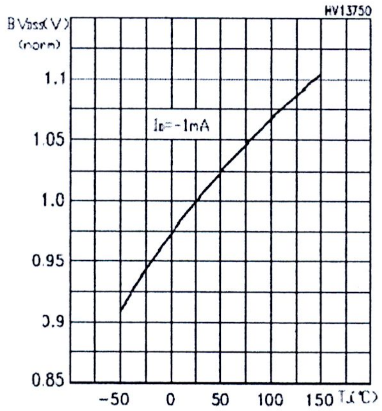
Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics



Normalized BVDSS vs Temperature



Maximum Avalanche Energy vs Temperature

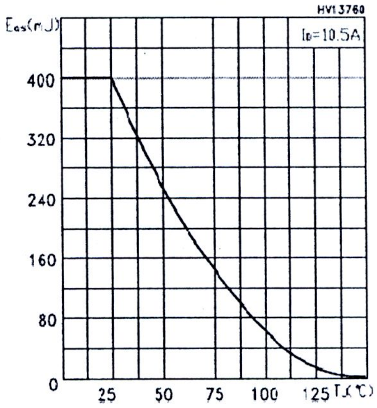


Fig. 1: Unclamped Inductive Load Test Circuit

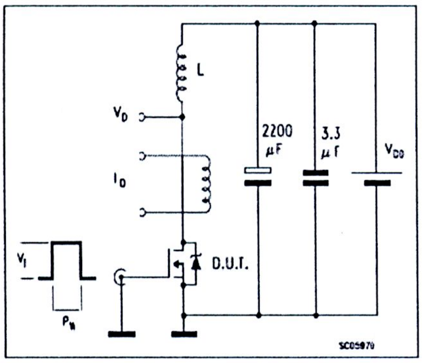


Fig. 2: Unclamped Inductive Waveform

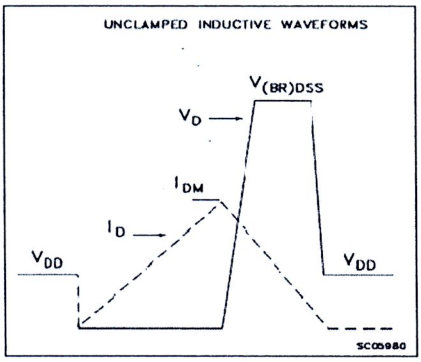


Fig. 3: Switching Times Test Circuit For Resistive Load

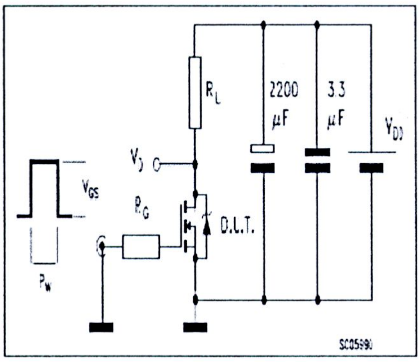


Fig. 4: Gate Charge test Circuit

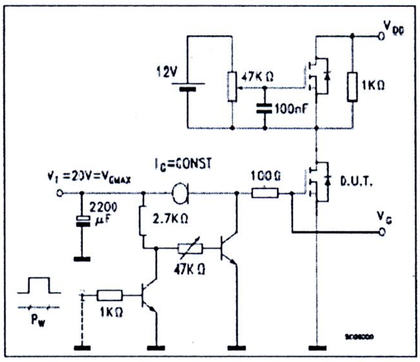
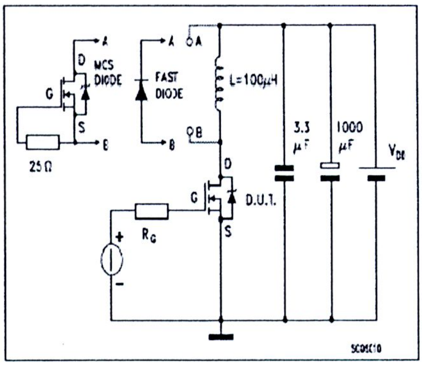


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



ประวัติผู้วิจัย

ดร.กองพล อารีรักษ์ สำเร็จการศึกษาในระดับปริญญาตรี โท และเอก ทางด้านวิศวกรรมไฟฟ้า จากมหาวิทยาลัยเทคโนโลยีสุรนารี จังหวัดนครราชสีมา ในปี พ.ศ. 2543 2546 และ 2550 ตามลำดับ ปัจจุบันดำรงตำแหน่งผู้ช่วยศาสตราจารย์ และหัวหน้าหน่วยวิจัยคุณภาพกำลังไฟฟ้า ประจำสาขาวิชาวิศวกรรมไฟฟ้า สำนักวิชาวิศวกรรมศาสตร์ มหาวิทยาลัยเทคโนโลยีสุรนารี มีความชำนาญทางด้านอิเล็กทรอนิกส์กำลัง วงจรกรองกำลังแอกทีฟ การขับเคลื่อนเครื่องจักรกลไฟฟ้า คุณภาพกำลังไฟฟ้า ระบบควบคุม และการประยุกต์ทางด้านปัญญาประดิษฐ์